

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4	("20030027360" "6060755").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:43
S2	4	("20030027360" "6060755").PN. and transistor and (semiconductor or wafer or substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:43
S3	0	("20030027360" "6060755").PN. and transistor and (semiconductor or wafer or substrate) and source and drain and (buffer or insulat\$4 or oxide or dielectric) and (ferroelectric near4 film) and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:45
S4	2477	transistor and (semiconductor or wafer or substrate) and source and drain and (buffer or insulat\$4 or oxide or dielectric) and (ferroelectric near4 film) and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:45
S5	22	transistor and (semiconductor or wafer or substrate) and source and drain and (buffer or insulat\$4 or oxide or dielectric) and (ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:50
S6	5	transistor and (semiconductor or wafer or substrate) and source and drain and (buffer or insulat\$4 or oxide or dielectric) and (ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide) and nitrogen	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:48

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S7	4	transistor and (semiconductor or wafer or substrate) and source and drain and (buffer or insulat\$4 or oxide or dielectric) and (ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide) and nitrogen and (anneal or heat)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:59
S8	1	transistor and (semiconductor or wafer or substrate) and source and drain and (buffer or insulat\$4 or oxide or dielectric) and (ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide) and nitrogen and (anneal or heat) and gas	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:49
S9	2	transistor and (semiconductor or wafer or substrate) and source and drain and (buffer or insulat\$4 or oxide or dielectric) and (ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide) and (nitrogen near4 gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 14:50
S10	4	(semiconductor or wafer or substrate) and source and drain and (buffer or insulat\$4 or oxide or dielectric) and (ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide) and nitrogen and (anneal or heat)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:00
S11	26	(ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:01
S12	26	(ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide) and (semiconductor or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:01

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S13	22	(ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide) and (semiconductor or substrate or wafer) and source and drain	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:01
S14	22	(ferroelectric near4 film) and gate and ((hafnium near4 aluminum) near4 oxide) and (semiconductor or substrate or wafer) and source and drain and (buffer or oxide or insulat\$4 or insulat\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:02
S15	22	(ferroelectric near4 film) and (gate near4 electrode) and ((hafnium near4 aluminum) near4 oxide) and (semiconductor or substrate or wafer) and source and drain and (buffer or oxide or insulat\$4 or insulat\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:02
S16	2	(ferroelectric near4 film) and (gate near4 electrode) and ((hafnium near4 aluminum) near4 oxide) and (semiconductor or substrate or wafer) and source and drain and (buffer or oxide or insulat\$4 or insulat\$4) and (nitrogen near4 gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:03
S17	15	(ferroelectric near4 film) and (gate near4 electrode) and ((hafnium near4 aluminum) near4 oxide) and (semiconductor or substrate or wafer) and source and drain and (buffer or oxide or insulat\$4 or insulat\$4) and (anneal or heat)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 07:59
S18	28	(ferroelectric near4 film) and ((hafnium near4 aluminum) near4 oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 08:02
S19	5	(ferroelectric near4 film) and ((hafnium near4 aluminum) near4 oxide) and (vessel or vacuum)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 08:02

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S20	2	(ferroelectric near4 film) and ((hafnium near4 aluminum) near4 oxide) and (vessel or vacuum) and nitrogen near4 gas	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 08:05
S21	6	(ferroelectric near4 film) and (hafnium near4 aluminum) and (vessel or vacuum) and (nitrogen near4 gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/01 08:06